NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI UTV005** is Designed for Class A, UHF Television – Band IV and V Applications up to 860 MHz.

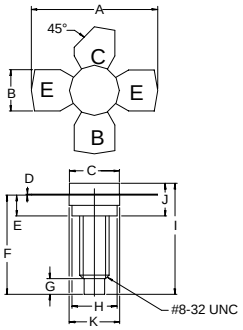
FEATURES:

- Common Emitter
- P_G = 11 dB at 0.5 W/470-860 MHz
- ***Omnigold***™ Metalization System

MAXIMUM RATINGS

I_C	0.75 A
V_{CEO}	24 V
V_{CES}	45 V
V_{EBO}	3.5 V
P_{DISS}	8.0 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	22 °C/W

PACKAGE STYLE .280 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	1.010 / 25.65	1.055 / 26.80
B	.220 / 5.59	.230 /5.84
C	.270 / 6.86	.285 / 7.24
D	.003 / 0.08	.007 / 0.18
E	.117 / 2.97	.137 / 3.48
F	.572 / 14.53	
G	.130 / 3.30	
H	.245 / 6.22	.255 / 6.48
I	.640 / 16.26	
J	.175 / 4.45	.217 / 5.51
K	.275 / 6.99	.285 / 7.24

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I_C = 20 mA	24			V
BV_{CES}	I_C = 10 mA	45			V
BV_{EBO}	I_E = 1.0 mA	3.5			V
h_{FE}	V_{CE} = 5.0 V I_C = 100 mA	20	---	---	---
C_{ob}	V_{CB} = 20 V f = 1.0 MHz		5.0		pF
P_G IMD^3 $VSWR_1$	V_{CC} = 20 V P_{OUT} = 0.5 W I_C = 220 mA f = 470-860 MHz		11 -60	 30:1	dB dB ---